

MCH6421-TL-W Datasheet



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DiGi Electronics Part Number MCH6421-TL-W-DG

Manufacturer onsemi

Manufacturer Product Number MCH6421-TL-W

Description MOSFET N-CH 20V 5.5A MCPH6

Detailed Description N-Channel 20 V 5.5A (Ta) 1.5W (Ta) Surface Mount

SC-88FL/MCPH6



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MCH6421-TL-W	onsemi
Series:	Product Status:
	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	5.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
1.8V, 4.5V	38mOhm @ 2A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.3V @ 1mA	5.1 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	410 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	1.5W (Ta)
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SC-88FL/MCPH6	6-TSSOP, SC-88, SOT-363
Base Product Number:	
MCH64	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

Power MOSFET 20V, $38m\Omega$, 5.5A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 1.8V drive
- High Speed Switching
- ESD Diode-Protected Gate
- Pb-Free and RoHS compliance
- Halogen Free compliance : MCH6421-TL-W

Typical Applications

- Load Switch
- Synchronous Boost Converter

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	٧
Gate to Source Voltage	VGSS	±12	٧
Drain Current (DC)	ID	5.5	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	22	Α
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

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Parameter	Symbol	Value	Unit			
Junction to Ambient When mounted on ceramic substrate (1200mm² × 0.8mm)	$R_{\theta JA}$	83.3	°C/W			

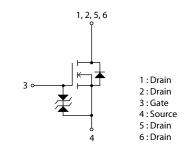


ON Semiconductor®

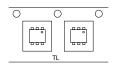
www.onsemi.com

VDSS	R _{DS} (on) Max	ID Max
	38mΩ@ 4.5V	
20V	61mΩ@ 2.5V	5.5A
	99mΩ@ 1.8V	

ELECTRICAL CONNECTION N-Channel



PACKING TYPE : TL





ORDERING INFORMATION

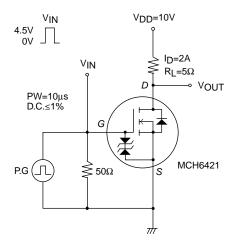
See detailed ordering and shipping information on page 5 of this data sheet.

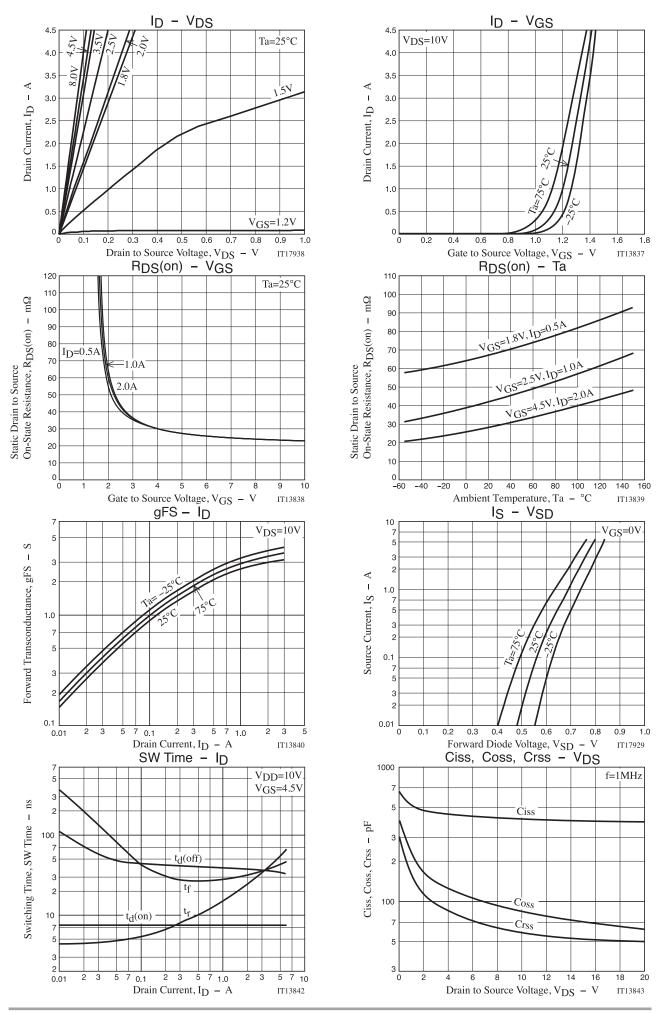
ELECTRICAL CHARACTERISTICS at $Ta = 25^{\circ}C$ (Note 2)

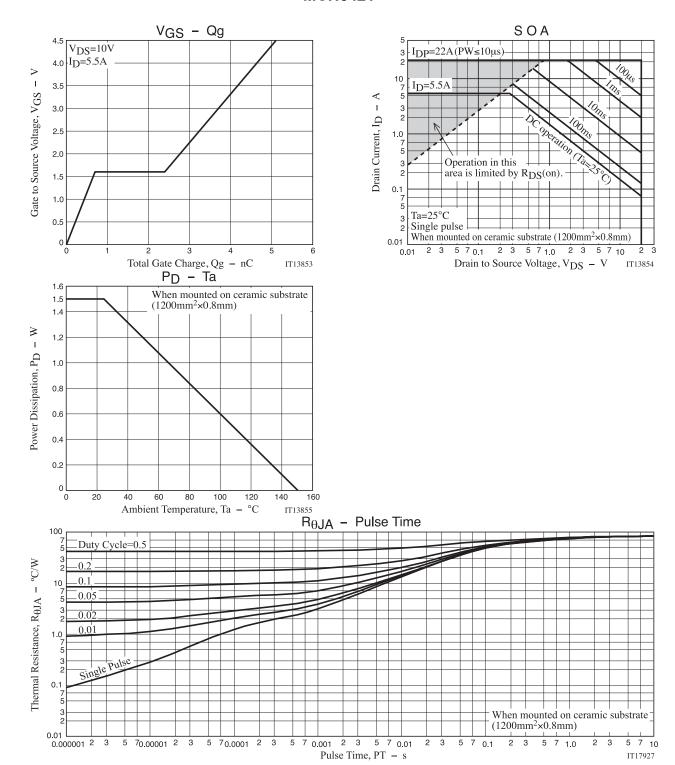
Parameter	Cumbal	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			٧
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transconductance	gFS	V _{DS} =10V, I _D =2A	2.0	3.8		S
	R _{DS} (on)1	I _D =2A, V _G S=4.5V		29	38	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _{GS} =2.5V		43	61	mΩ
	RDS(on)3	I _D =0.5A, V _{GS} =1.8V		69	99	mΩ
Input Capacitance	Ciss			410		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		84		pF
Reverse Transfer Capacitance	Crss			59		pF
Turn-ON Delay Time	t _d (on)			7.5		ns
Rise Time	tr	See specified Test Circuit		26		ns
Turn-OFF Delay Time	t _d (off)			38		ns
Fall Time	tf			32		ns
Total Gate Charge	Qg			5.1		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =5.5A		0.7		nC
Gate to Drain "Miller" Charge	Qgd			1.7		nC
Forward Diode Voltage	V _{SD}	IS=5.5A, VGS=0V		0.8	1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit

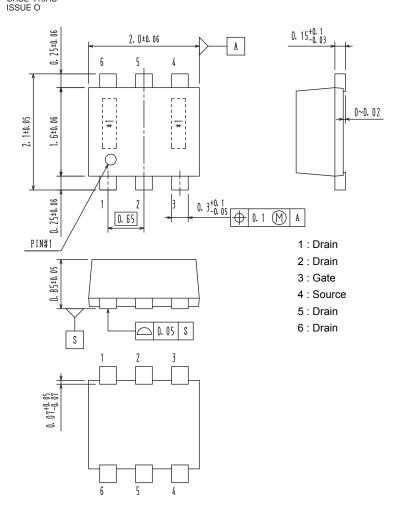




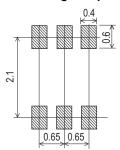


PACKAGE DIMENSIONS

unit: mm SC-88FL/MCPH6 CASE 419AS ISSUE O



Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
MCH6421-TL-E	107	SC-88FL / MCPH6 (Pb-Free)	3,000 / Tape & Reel	
MCH6421-TL-W	NV .	SC-88FL / MCPH6 (Pb-Free / Halogen Free)	5,000 / Tape & Reel	

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6421 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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